

# **BUK7E3R1-40E**

# N-channel TrenchMOS standard level FET 11 September 2012

**Product data sheet** 

#### **Product profile** 1.

# 1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

# 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

# 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

# 1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	234	W
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		-	2.6	3.1	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; Fig. 13; Fig. 14		-	22	-	nC

[1] Continuous current is limited by package.



# 2. Pinning information

**Table 2.** Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D 
2	D	drain		
3	S	source		G THE
mb	D	mounting base; connected to drain		mbb076 S
			I2PAK (SOT226)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package	e					
	Name	Description	Version				
BUK7E3R1-40E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226				

# 4. Marking

Table 4. Marking codes

Type number	Marking code
BUK7E3R1-40E	BUK7E3R1-40E

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	40	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; <u>Fig. 1</u>	[1]	-	100	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	798	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	234	W
T <sub>stg</sub>	storage temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode		'		'	
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	798	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 100 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	419	mJ

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

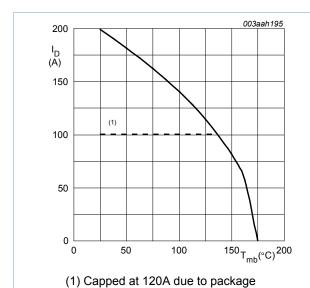


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

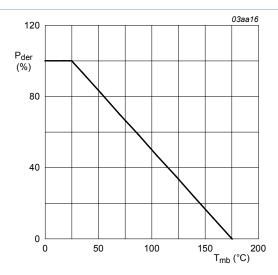


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}C)}} \times 100 \,\%$$

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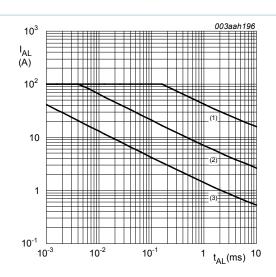
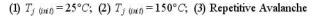


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



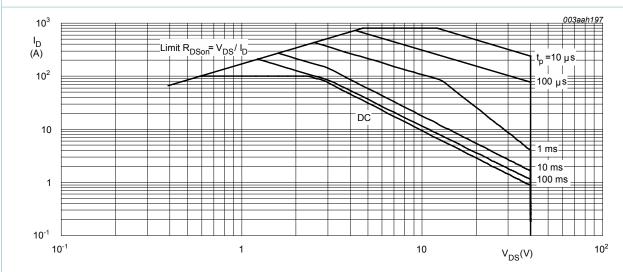


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

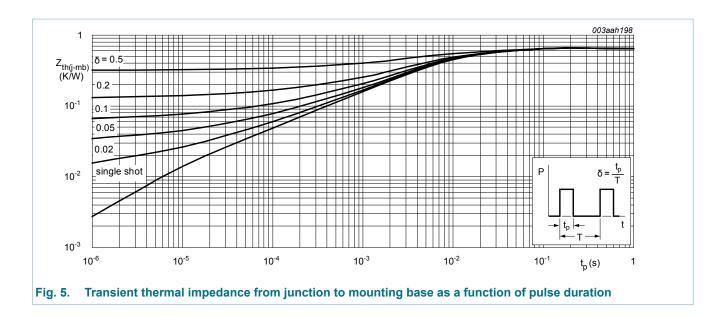
# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	0.64	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air	-	65	-	K/W

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# 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics			'			
V <sub>(BR)DSS</sub> drain-source breakdown voltage		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V	
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	36	-	-	V	
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V	
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.2	2	μΑ	
	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ		
I <sub>GSS</sub> gate leakage curre	I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11	-	2.6	3.1	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	5.9	mΩ	
Dynamic ch	naracteristics			'		,	
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	79	-	nC	
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	20	-	nC	
Q <sub>GD</sub>	gate-drain charge	1	-	22	-	nC	

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;		-	4650	6200	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	885	1065	pF
C <sub>rss</sub>	reverse transfer capacitance			-	470	640	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 1.2 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 5 $\Omega$		-	24	-	ns
t <sub>r</sub>	rise time			-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	54	-	ns
t <sub>f</sub>	fall time			-	32	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die		-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad		-	7.5	-	nH
Source-dra	in diode		1				1
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	38.8	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	44.6	-	nC

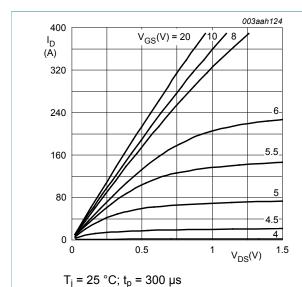


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

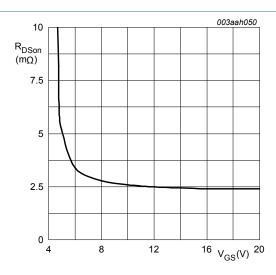


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

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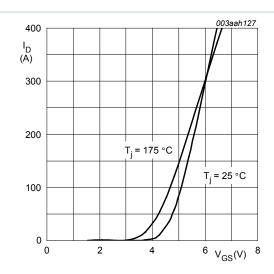


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



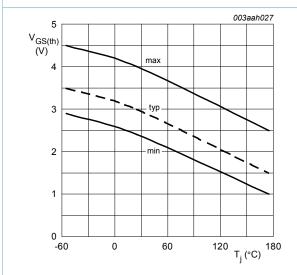


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

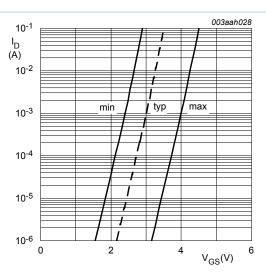
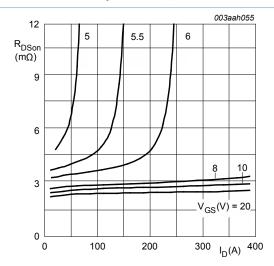


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$



 $T_j = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

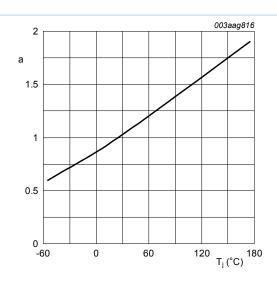


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25~\mathrm{C})}}$$

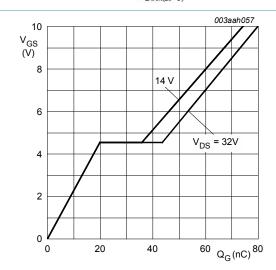


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C;  $I_D = 25$ A

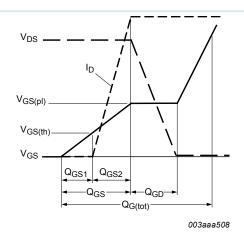


Fig. 13. Gate charge waveform definitions

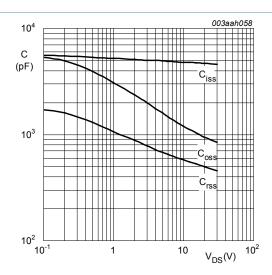


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

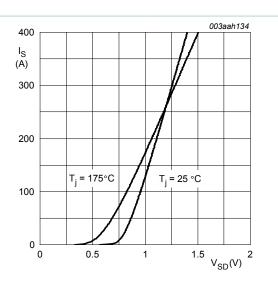


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

# 8. Package outline

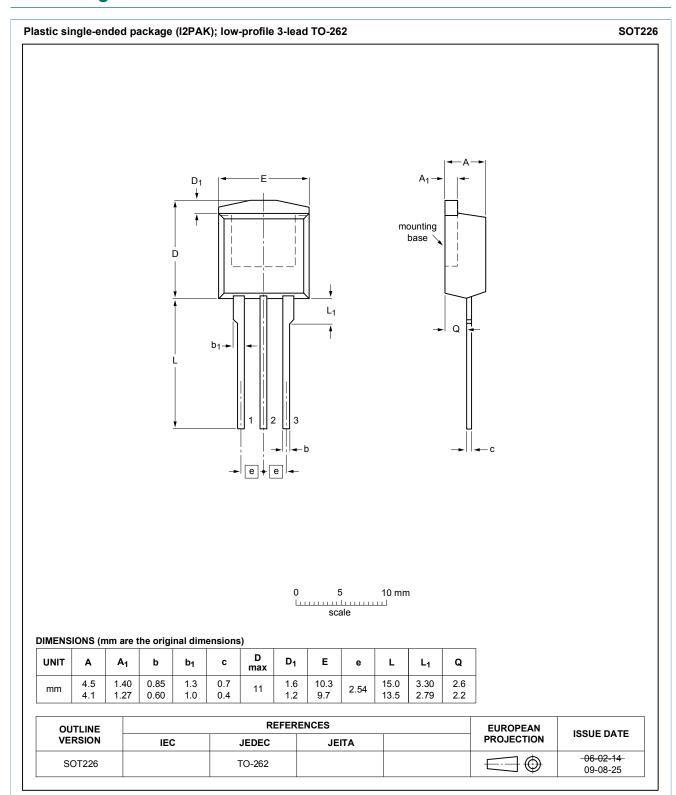


Fig. 17. Package outline I2PAK (SOT226)

# 9. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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